

## HIGH-SPEED 3.3V 1K X 8 DUAL-PORT STATIC RAM

#### Features High-speed access On-chip port arbitration logic Interrupt flags for port-to-port communication - Commercial: 25/55ns (max.) Fully asynchronous operation from either port - Industrial 35ns (max.) ٠ Battery backup operation, 2V data retention (L Only) Low-power operation TTL-compatible, single 3.3V ±0.3V power supply - IDT71V30S ٠ Industrial temperature range (-40°C to +85°C) is available Active: 375mW (typ.) for selected speeds Standby: 5mW (typ.) ٠ Green parts available, see ordering information - IDT71V30L Active: 375mW (typ.) Standby: 1mW (typ.)

## Functional Block Diagram



- 1. IDT71V30: BUSY outputs are non-tristatable push-pulls.
- 2. INT outputs are non-tristable push-pull output structure.

71V30S/L High-Speed 1K x 8 Dual-Port Static RAM with Interrupts

Industrial and Commercial Temperature Ranges

### Description

The IDT71V30 is a high-speed 1K x 8 Dual-Port Static RAM. The IDT71V30 is designed to be used as a stand-alone 8-bit Dual-Port SRAM.

Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by  $\overline{CE}$ , permits the on chip circuitry of each port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 375mW of power. Low-power (L) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT71V30 devices are packaged in 64-pin STQFPs.

### Pin Configurations<sup>(1,2,3)</sup>



- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. Package body is approximately 10mm x 10mm x 1.4mm.
- 4. This package code is used to reference the package diagram.

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### Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Com'l & Ind	Unit
Vterm <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +4.60	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Tjn(3)	Junction Temperature	+150	٥C
lout	DC Output Current	50	mA

#### NOTES:

3741 tbl 01

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 0.3V.
- 3. This is the absolute maximum junction temperature for the device. No DC Bias.

### Capacitance<sup>(1)</sup> (TA = +25°C, f=1.0MHz)

Symbol	Parameter	Conditions <sup>(2)</sup>	Max.	Unit				
Cin	Input Capacitance	VIN = 3dV	9	pF				
Cout <sup>(3)</sup>	Output Capacitance	Vout = 3dV	10	pF				
3741 tb								

NOTES:

 This parameter is determined by device characterization but is not production tested.

3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

#### Industrial and Commercial Temperature Ranges

### Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
V⊪	Input High Voltage	2.0		VCC+0.3V	V
Vil	Input Low Voltage	-0.3(1)	_	0.8	V

NOTE:

1. VIL (min.) = -1.5V for pulse width less than 20ns.

### Maximum Operating Temperature and Supply Voltage<sup>(1,2)</sup>

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3
			3741 tbl 03

#### NOTES:

2. Industrial temperature: for specific speeds, packages and powers, contact your sales office.

### DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

			71V30S		71V		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Мах.	Unit
LI	Input Leakage Current <sup>(1)</sup>	$V_{CC} = 3.6V,$ $V_{IN} = 0V$ to $V_{CC}$	_	10	Í	5	μA
Ilo	Output Leakage Current	$\overline{CE} = VIH,$ Vout = 0V to Vcc		10	_	5	μA
Vol	Output Low Voltage (I/Oo-I/O7)	Iol = 4mA		0.4	—	0.4	V
Vон	Output High Voltage	Іон = -4mA	2.4	_	2.4		V

NOTE:

At Vcc ≤ 2.0V input leakages are undefined.

3741 tbl 05

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<sup>1.</sup> This is the parameter TA. This is the "instant on" case temperature.

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## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1,6,7)</sup> (Vcc = $3.3V \pm 0.3V$ )

				Version		71V30X25 Com'l Only		0X35 & Ind	71V30X55 Com'l Only		
Symbol	Parameter	Test Condition	Versi			Max.	Typ. <sup>(2)</sup>	Max.	Typ. <sup>(2)</sup>	Max.	Uni
lcc	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL, Outputs Disabled	COM'L	S L	75 75	150 120	75 75	145 115	75 75	135 105	mA
		f = fmax <sup>(3)</sup>	IND	S L			— 75	 145			
	Standby Current (Both Ports - TTL Level Inputs)	CEL and CER= VIL, $f = f_{MAX}^{(3)}$	COM'L	S L	20 20	50 35	20 20	50 35	20 20	50 35	m/
			IND	S L			 20	 50			
(	Standby Current (One Port - TTL Level Inputs)	$CE^{*}A^{*} = VIL$ and $CE^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled, $f=f_{MAX}^{(3)}$	COM'L	S L	30 30	105 75	30 30	100 70	30 30	90 60	m/
			IND	S L			 30	 100			
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CEL and CER $\geq$ Vcc - 0.2V VN $\geq$ Vcc - 0.2V or Vm $= 0.2V$ f $= 0.2V$	COM'L	S L	1.0 0.2	5.0 3.0	1.0 0.2	5.0 3.0	1.0 0.2	5.0 3.0	m/
		$V_{IN} \leq 0.2V, f = 0^{(4)}$	IND	S L	_		 1.0	 5.0			
ISB4	Full Standby Current (One Port - CMOS	CE"B" ≥ Vcc - 0.2V <sup>(5)</sup> ViN ≥ Vcc - 0.2V or ViN ≤ 0.2V	COM'L	S L	30 30	90 75	30 30	85 70	30 30	75 60	m/
			IND	S L				— 85	_		

NOTES:

1. 'X' in part number indicates power rating (S or L)

2. Vcc = 3.3V, TA = +25°C, and are not production tested. Icccc = 70mA (Typ.)

3. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6. Refer to chip enable Truth Table I.

7. Industrial temperature: for specific speeds, packages and powers contact your sales office.

### Data Retention Characteristics (L Version Only)

				71V30L			
Symbol	Parameter	Test Condition		Min.	Typ. <sup>(1)</sup>	Max.	Unit
Vdr	Vcc for Data Retention			2.0			V
ICCDR	Data Retention Current		Ind.		100	1000	μA
		$Vcc = 2V, \overline{CE} \ge Vcc - 0.2V$	Com'l.		100	500	
tcdr <sup>(3)</sup>	Chip Deselect to Data Retention Time	$V\textsc{in} \geq V\textsc{cc}$ -0.2V or $V\textsc{in} \leq 0.2V$		0			ns
tR <sup>(3)</sup>	Operation Recovery Time			tRC <sup>(2)</sup>			ns

NOTES:

1. Vcc = 2V, TA =  $+25^{\circ}$ C, and is not production tested.

2. tRc = Read Cycle Time.

3. This parameter is guaranteed by device characterization but not production tested.



# AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(3,4)</sup>

		71V30X25 Com'l Only		71V30X35 Com'l & Ind		71V30X55 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	25		35		55		ns
taa	Address Access Time		25	-	35		55	ns
tace	Chip Enable Access Time		25		35		55	ns
taoe	Output Enable Access Time	_	12	_	20		25	ns
toн	Output Hold from Address Change	3	_	3		3		ns
tlz	Output Low-Z Time <sup>(1,2)</sup>	0		0		0		ns
tнz	Output High-Z Time <sup>(1,2)</sup>	_	12		15		30	ns
tpu	Chip Enable to Power Up Time <sup>(2)</sup>	0		0		0		ns
tpd	Chip Disable to Power Down Time <sup>(2)</sup>		50	_	50		50	ns

NOTES:

1. Transition is measured 0mV from Low- or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

3. 'X' in part number indicates power rating (S or L).

4. Industrial temperature: for specific speeds, packages and power contact your sales office.

3741 tbl 09



#### NOTES:

- 1.  $R/\overline{W} = V_{IH}$ ,  $\overline{CE} = V_{IL}$ , and is  $\overline{OE} = V_{IL}$ . Address is valid prior to the coincidental with  $\overline{CE}$  transition LOW.
- 2. tbbb delay is required only in case where the opposite is port is completing a write operation to same the address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last taoe, tace, taa, and tBDD.

## Timing Waveform of Read Cycle No. 2, Either Side<sup>(3)</sup>



#### NOTES:

- 1. Timing depends on which signal is asserted last,  $\overline{OE}$  or  $\overline{CE}$ .
- 2. Timing depends on which signal is desserted first, OE or CE.

3.  $R/\overline{W} = V_{H}$  and the address is valid prior to or coincidental with  $\overline{CE}$  transition LOW.

4. Start of valid data depends on which timing becomes effective last tAOE, tACE, and tBDD.

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## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage<sup>(4,5)</sup>

			71V30X25 Com'l Only		71V30X35 Com'l & Ind		71V30X55 Com'l Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE C	YCLE					-		
twc	Write Cycle Time	25		35		55		ns
tew	Chip Enable to End-of-Write	20		30		40		ns
taw	Address Valid to End-of-Write	20		30		40		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width	20		30		40		ns
twr	Write Recovery Time	0		0		0		ns
tdw	Data Valid to End-of-Write	12		20		20		ns
tHZ	Output High-Z Time <sup>(1,2)</sup>		12		15		30	ns
tdн	Data Hold Time <sup>(3)</sup>	0		0		0		ns
twz	Write Enable to Output in High-Z <sup>(1,2)</sup>		15		15		30	ns
tow	Output Active from End-of-Write <sup>(1,2,3)</sup>	0		0		0		ns

NOTES:

1. Transition is measured 0mV from Low- or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

3. The specification for tDH must be met by the device supplying write data to the SRAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

4. 'X' in part number indicates power rating (S or L).

5. Industrial temperatures: for specific speeds, packages and powers contact your sales office.

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Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)<sup>(1,5,8)</sup>



Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing<sup>(1,5)</sup>



- 1.  $R/\overline{W}$  or  $\overline{CE}$  must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of  $\overline{CE} = V_{IL}$  and  $R/\overline{W} = V_{IL}$ .
- 3. two is measured from the earlier of  $\overline{CE}$  or  $R/\overline{W}$  going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal ( $\overline{CE}$  or  $R/\overline{W}$ ) is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If  $\overline{OE}$  is LOW during a RW controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If  $\overline{OE}$  is HIGH during a RW controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

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## AC Electrical Characteristics Over the

Operatin	g Tempe	erature and	Supply	Voltage	Range <sup>(6,7)</sup>
				J	J

	71V30X25 Com'l Only			71V30X35 Com'l & Ind		71V30X55 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIM	ING (M/S=Vih)	-						
tbaa	BUSY Access Time from Address Match		20	_	20		30	ns
tbda	BUSY Disable Time from Address Not Matched		20		20		30	ns
<b>t</b> BAC	BUSY Access Time from Chip Enable		20		20		30	ns
tBDC	BUSY Disable Time from Chip Enable		20		20		30	ns
twн	Write Hold After BUSY <sup>(5)</sup>	20	_	30		40		ns
twdd	Write Pulse to Data Delay <sup>(1)</sup>		50	_	60		80	ns
tddd	Write Data Valid to Read Data Delay <sup>(1)</sup>		35		45		65	ns
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5		5		5		ns
tbdd	BUSY Disable to Valid Data <sup>(3)</sup>		30		30		45	ns

NOTES:

3741 tbl 11

1. Port-to-port delay through SRAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read with BUSY".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual) or tDDD - tDw (actual).

4. To ensure that the Write Cycle is inhibited on Port "B" during contention on Port "A".

5. To ensure that the Write Cycle is completed on Port "B" after contention on Port "A".

6. 'X' in part number indicates power rating (S or L).

7. Industrial temperature: for specific speeds, packages and powers contact your sales office.

## Timing Waveform of Write with Port-to-Port Read with **BUSY**<sup>(1,2,3,4)</sup>



#### NOTES:

1. To ensure that the earlier of the two ports wins.

2.  $\overline{CE}L = \overline{CE}R = VIL$ 

3.  $\overline{OE} = V_{IL}$  for the reading port.

4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".



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### Timing Waveform of Write with **BUSY**<sup>(3)</sup>



NOTES:

twH must be met for BUSY.
BUSY is asserted on port 'B' blocking R/WB', until BUSY'B' goes HIGH.

All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

## Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing<sup>(1)</sup>



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.

## Timing Waveform of **BUSY** Arbitration Controlled Address Match Timing<sup>(1)</sup>



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.

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### AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1,2)</sup>

		71V30X25 71V30X35 Com'l Only Com'l & Ind		71V30X55 Com'l Only				
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Мах.	Unit
INTERRUP	PT TIMING							
tas	Address Set-up Time	0		0		0		ns
twr	Write Recovery Time	0		0		0		ns
tins	Interrupt Set Time	_	25		25	-	45	ns
tinr	Interrupt Reset Time		25		25		45	ns
							3	741 tbl 12

NOTES:

1. 'X' in part number indicates power rating (S or L).

2. Industrial temperature: for specific speeds, packages and powers contact your sales office.

## Timing Waveform of Interrupt Mode<sup>(1)</sup>



**INT** Clears



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table II.
- 3. Timing depends on which enable signal ( $\overline{CE}$  or  $R/\overline{W}$ ) is asserted last.
- 4. Timing depends on which enable signal (CE or R/W) is de-asserted first.

#### 71V30S/L High-Speed 1K x 8 Dual-Port Static RAM with Interrupts

#### Truth Tables

### Table I — Non-Contention Read/Write Control<sup>(4)</sup>

Left or Right Port <sup>(1)</sup>				
R/W	CE	ŌĒ	D0-7	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	$\overline{CER} = \overline{CEL} = V_{IH}$ , Power-Down Mode, ISB1 or ISB3
L	L	Х	DATAIN	Data on Port Written Into Memory <sup>(2)</sup>
Н	L	L	DATAOUT	Data in Memory Output on Port <sup>(3)</sup>
Н	L	Н	Z	High Impedance Outputs

NOTES:

1. AOL – A9L  $\neq$  AOR – A9R.

2. If  $\overline{\text{BUSY}}$  = L, data is not written.

3. If  $\overline{\text{BUSY}}$  = L, data may not be valid, see twop and topp timing.

4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

### Table II — Interrupt Flag<sup>(1,4)</sup>

	Left Port									
R/₩L	CEL	OEL	A9L-A0L	ĪNT∟	R/WR	ĊĒr		A9R-A0R	Ī <b>NT</b> R	Function
L	L	Х	3FF	Х	Х	Х	Х	Х	L <sup>(2)</sup>	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	3FF	H <sup>(3)</sup>	Reset Right INTR Flag
Х	Х	Х	Х	L <sup>(3)</sup>	L	L	Х	3FE	Х	Set Left INTL Flag
Х	L	L	3FE	H <sup>(2)</sup>	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

1. Assumes  $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = V_{IH}$ 

2. If  $\overline{\text{BUSY}}_{L} = V_{IL}$ , then No Change.

3. If  $\overline{\text{BUSY}}_{R} = V_{IL}$ , then No Change.

4. 'H' = HIGH,' L' = LOW,' X' = DON'T CARE

### Table III — Address **BUSY** Arbitration

	In	puts	Out	puts	
Ē	<b>CE</b> R	Aol-A9l Aor-A9r	BUSYL <sup>(1)</sup>	BUSY <sub>R</sub> <sup>(1)</sup>	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

#### NOTES:

1. Pins BUSYL and BUSYR are both outputs for IDT71V30. BUSYX outputs on the IDT71V30 are non-tristatable push-pull.

 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

 Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

3741 tbl 15

3741 tbl 14

3741 tbl 13

#### 71V30S/L High-Speed 1K x 8 Dual-Port Static RAM with Interrupts

#### Industrial and Commercial Temperature Ranges

#### Functional Description

The IDT71V30 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71V30 has an automatic power down feature controlled by CE. The CE controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{CE} = V_{H}$ ). When a port is enabled, access to the entire memory array is permitted.

### Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ( $\overline{INTL}$ ) is asserted when the right port writes to memory location 3FE (HEX), where a write is defined as the  $\overline{CE} = R/\overline{W} = V_{IL}$  per Truth Table II. The left port clears the interrupt by accessing address location 3FE access with  $\overline{CER} = \overline{OER} = V_{IL}$ ,  $R/\overline{W}$  is a "don't care". Likewise, the right port interrupt flag ( $\overline{INTR}$ ) is asserted when the left port writes to memory location 3FF (HEX) and to clear the interrupt flag ( $\overline{INTR}$ ), the right port must access the memory location 3FF. The message (8 bits)

at 3FE or 3FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FE and 3FF are not used as mail boxes, and are part of the random access memory. Refer to Table II for the interrupt operation.

### **Busy Logic**

Busy Logic provides a hardware indication that both ports of the SRAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the SRAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of  $\overline{\text{BUSY}}$  logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{\text{BUSY}}$  outputs together and use any  $\overline{\text{BUSY}}$  indication as an interrupt source to flag the event of an illegal or illogical operation.

71V30 High-S		x 8 Dua	I-Port Stati	ic RAM	with Interrup	ts	Ind	lustrial and Commercial Temperature Range
Orde	ring	Infor	matio	n				
XXXXX Device Type	A Power	99 Speed	A Package		A A Process/ Temperature Range		Blank 8 Blank I <sup>(1)</sup> G	Tray Tape and Reel Commercial (0°C to +70°C) Industrial (-40°C to +85°C) Green 64-pin STQFP (PPG64)
							25 35 55	Commercial Only Industrial Only Commercial Only
							 S L	Standard Power Low Power
							 71V30	8K (1K x 8-Bit) Synchronous Dual-Port RAM 3741 drw 20

#### NOTES:

- 1. Contact your sales office for Industrial Temperature range in other speeds, packages and powers.
- 2. LEAD FINISH (SnPb) are Obsolete Product Discontinuation Notice PDN#SP-17-02

Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

## Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
25	71V30L25TFG	PPG64	TQFP	С
	71V30L25TFG8	PPG64	TQFP	С
35	71V30L35TFGI	PPG64	TQFP	I
	71V30L35TFG18	PPG64	TQFP	I

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade	
55	71V30S55TFG	PPG64	TQFP	С	
	71V30S55TFG8	PPG64	TQFP	С	

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## Datasheet Document History

12/09/98:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Added additional notes to pin configurations
06/15/99:	Changed drawing format
08/03/99:	Page 2 Fixed typographical error
09/01/99:	Removed Preliminary
11/12/99:	Replaced IDT logo
01/17/01:	Pages 1 and 2 Moved all of "Description" to page 2 and adjusted page layouts
	Page 3 Increased storage temperature parameters
	Clarified TA parameter
	Page 4 DC Electrical parameters-changed wording from "open" to "disabled"
	Changed ±200mV to 0mV in notes
03/14/05:	Page 1 Added green availability to features
	Page 17 Added green indicator to ordering information
	Page 1 & 17 Replaced old ™ logo with new ™ logo
07/16/07:	Page 3 Added Junction Temperature spec values to the Absolute Maximum Rating table
	Added footnote 3 for additional clarification of Junction Temperature
10/23/08:	Page 14 Removed "IDT" from orderable part number
11/25/09:	Page 4 In order to correct the DC Chars table for the 71V30L35 speed grade and to the Data Retention Chars table, I Temp
	values have been added to each table respectively. In addition, all of the AC tables and the ordering information also
	now reflect this I temp correction
06/22/15:	Page 2 Removed IDT in reference to fabrication
	Page 2 & 14 The package code PP64-1 changed to PP64 to match standard package codes
	Page 14 Added Tape and Reel indicator to Ordering Information
07/23/15:	Entire datasheet Removed the 55ns Industrial speed offering. 55ns speed only offered in commercial grade
12/20/17:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
06/24/19:	Page 1 & 14 Deleted obsolete Commercial speed grade 35ns in Features and Ordering Information
	Page 2 Rotated PPG64 STQFP pin configuration to accurately reflect pin 1 orientation

Page 14 Added Orderable Part Information tables